IN THE CLAIMS:

Please cancel claims 22-39, 48-49, 52 and 56 without prejudice or disclaimer, amend claims 50-51 as follows:

1-49. (Cancelled)

50. (Currently Amended) A crystal growing method, comprising the steps of:

forming a step-terrace structure on said SiC surface; [[;]]

removing an oxide film which is naturally formed on said surface in an atmosphere of reduced oxygen partial pressure and covers the step-terrace structure;

after the removing step, performing at least one cycle of a process including irradiating Si or Ga atomic beam on the surface and then heating the irradiated surface thereby separating said Ga or Si from the irradiated surface and removing oxygen on the surface to provide a flat and clean SiC surface; and

after the performing step, growing a Group-III nitride on the surface without said Ga or Si left in-between while the step-terrace structure is maintained, by adjusting a pre-feeding time of a Group-III element thereby preventing excess aggregation or lack of the Group-III element, feeding [[a]] the Group III element and feeding nitrogen after the Group III element has been fed.

51. (Currently Amended) [[The]]A crystal growing method ~~according to claim 22~~, comprising the steps of:

forming a step-terrace structure that is flat at an atomic level on a SiC surface and then removing an oxide film, which is naturally formed thereon and covers the step-terrace structure, from the surface;

after the forming and then removing step, performing at least one cycle of a process including irradiating Si or Ga atomic beam on the surface and then heating the irradiated surface thereby separating said Ga or Si from the irradiated surface and removing oxygen on the surface; and

after the performing step, growing a Group-III nitride on the surface,

wherein the Group-III nitride contains Al, and the step of growing a Group-III nitride is conducted under high vacuum and comprises the steps of:

step-flow-feeding Ga or In as a surface controlling element [[for]] thereby controlling the mode of crystal growth [[to be]] as layer-by-layer of the Group-III

nitride on said SiC surface, and each layer of the Group-III nitride consisting of fused two-dimensional nuclei of the Group-III nitride; and then

feeding a Group III element and nitrogen, followed by the termination of the feeding of said surface controlling element.

52. (Cancelled)

53. (Withdrawn) A heterojunction MISFET comprising:

a SiC substrate;

an AIN layer formed by forming a step-terrace structure on a SiC surface and then removing an oxide film on the surface, performing at least one cycle of a process of irradiation of Si or Ga and then heating, and growing a Group-III nitride;

a gate electrode formed on said AIN layer; and

a source and a drain formed on either side of said gate electrode.

54. (Withdrawn) A heterojunction laser device comprising:

a SiC substrate;

an MN buffer layer formed by forming a step-terrace structure on a SiC surface and then removing an oxide film on the surface, performing at least one cycle of a process of irradiation of Si or Ga and then heating, and growing a Group-III nitride;

a first AlGaN cladding layer formed on said AIN layer;

a GaN/InGaN multiquantum well structure; and

a second AlGaN cladding layer formed on said multiquantum well structure.

55. (Previously Presented) The crystal growing method according to claim 51, wherein the surface controlling element is either fed in a form of gas or irradiated on the surface in a form of an atomic beam.

56. (Cancelled)

57. (Previously Presented) The crystal growing method according to claim 50, wherein said SiC surface has an offset angle of 0-15° with respect to the (0001) Si or (000-1) C plane.

58. (Previously Presented) The crystal growing method according to claim 51, wherein said SiC surface has an offset angle of 0-15° with respect to the (0001) Si or (000-1) C plane.